
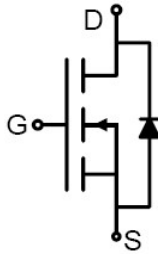


Description

Features <ul style="list-style-type: none"> ● 30V, 4A $R_{DS(ON)} < 38m\Omega @ V_{GS} = 10V$ $R_{DS(ON)} < 65m\Omega @ V_{GS} = 4.5V$ ● Advanced Trench Technology ● Excellent $R_{DS(ON)}$ and Low Gate Charge ● Lead free product is acquired 	Application <ul style="list-style-type: none"> ● Load Switch ● PWM Application ● Power management
 <p>SOT-23-3</p>	 <p>Schematic Diagram</p>

Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
VSM3406A-S2	VSM3406A	TAPING	SOT-23-3	7inch	3000	180000

Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		30	V
V_{GSS}	Gate-Source Voltage		± 20	V
I_D	Continuous Drain Current	$T_A = 25^{\circ}C$	4	A
		$T_A = 100^{\circ}C$	2.6	A
I_{DM}	Pulsed Drain Current ^{note1}		16	A
P_D	Power Dissipation	$T_A = 25^{\circ}C$	1	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		125	$^{\circ}C/W$
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	$^{\circ}C$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance <small>note2</small>	V _{GS} =10V, I _D =4A	-	29	38	mΩ
		V _{GS} =4.5V, I _D =3A	-	45	65	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1.0MHz	-	233	-	pF
C _{oss}	Output Capacitance		-	44	-	pF
C _{rss}	Reverse Transfer Capacitance		-	33	-	pF
Q _g	Total Gate Charge	V _{DS} =15V, I _D =2A, V _{GS} =10V	-	3	-	nC
Q _{gs}	Gate-Source Charge		-	0.5	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	0.8	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =15V, I _D =4A, R _{GEN} =3Ω, V _{GS} =10V	-	4	-	ns
t _r	Turn-on Rise Time		-	2.1	-	ns
t _{d(off)}	Turn-off Delay Time		-	15	-	ns
t _f	Turn-off Fall Time		-	3.2	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	4	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	16	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =4A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Typical Performance Characteristics

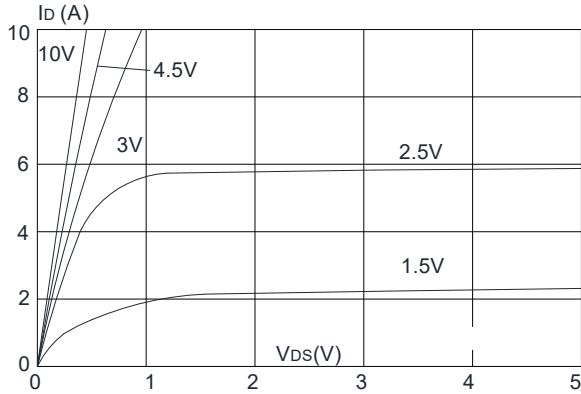
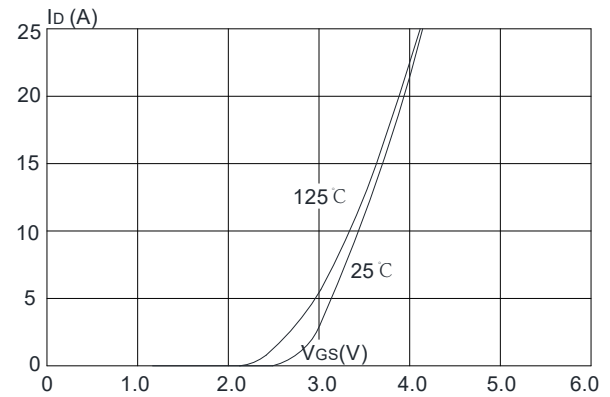
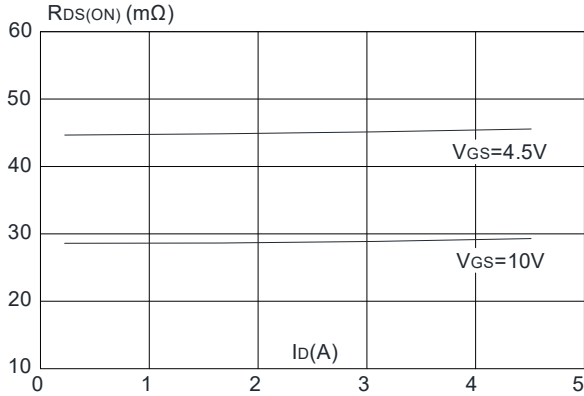
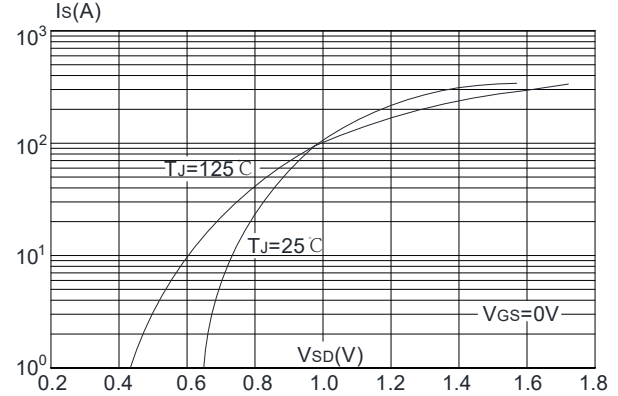
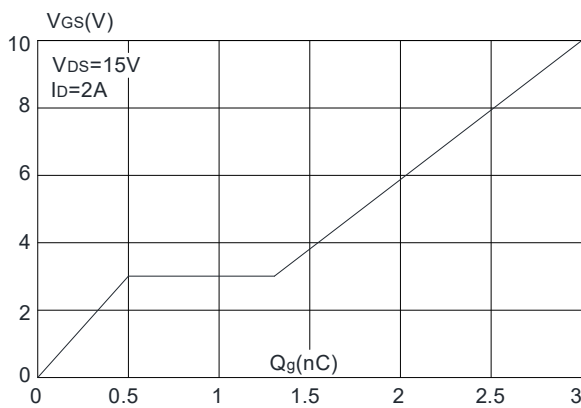
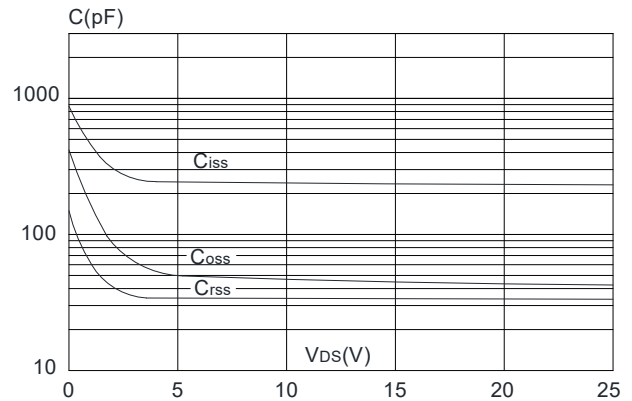
Figure1: Output Characteristics

Figure 2: Typical Transfer Characteristics

Figure 3: On-resistance vs. Drain Current

Figure 4: Body Diode Characteristics

Figure 5: Gate Charge Characteristics

Figure 6: Capacitance Characteristics


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

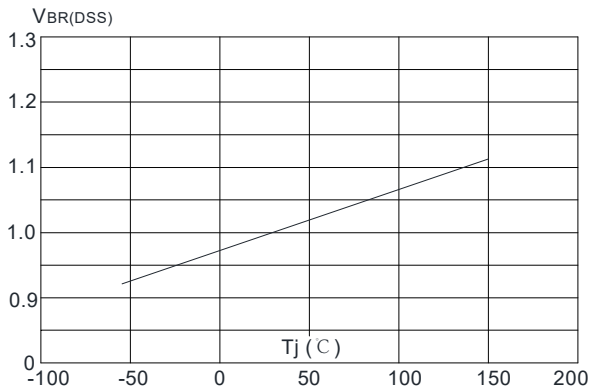


Figure 8: Normalized on Resistance vs. Junction Temperature

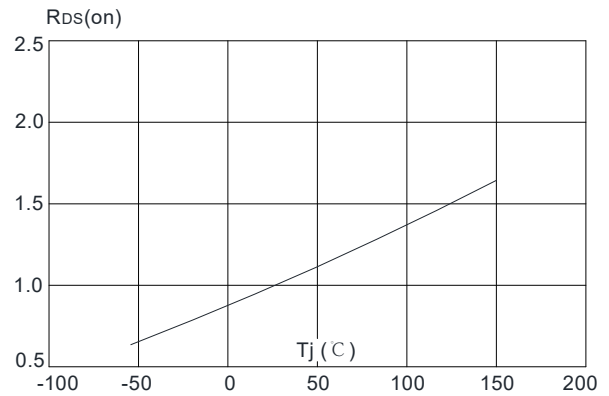


Figure 9: Maximum Safe Operating Area

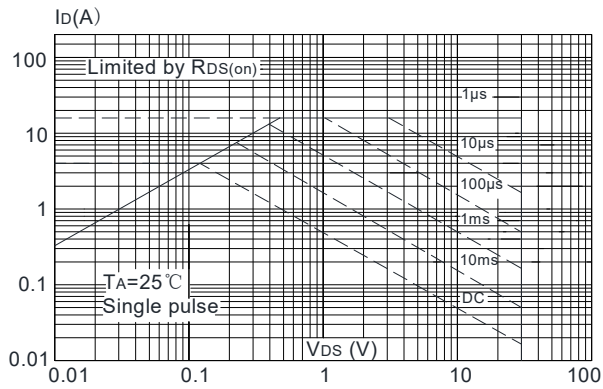


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

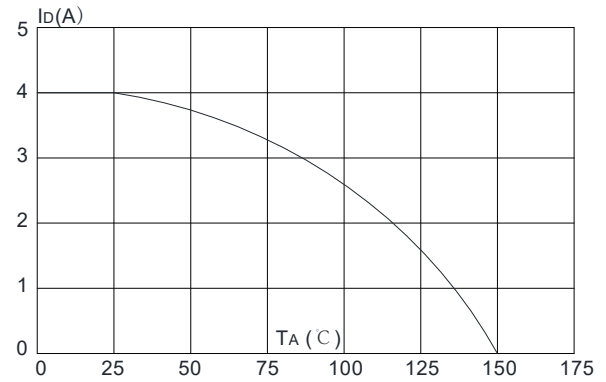
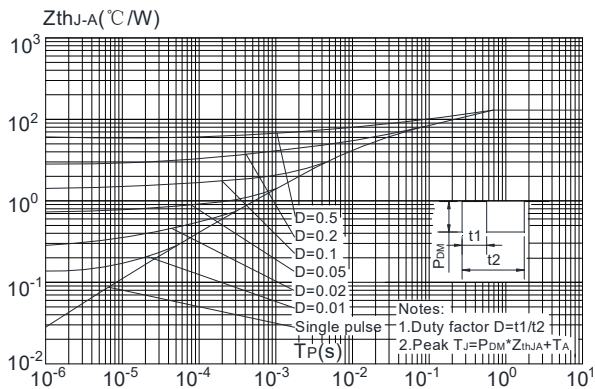


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Test Circuit

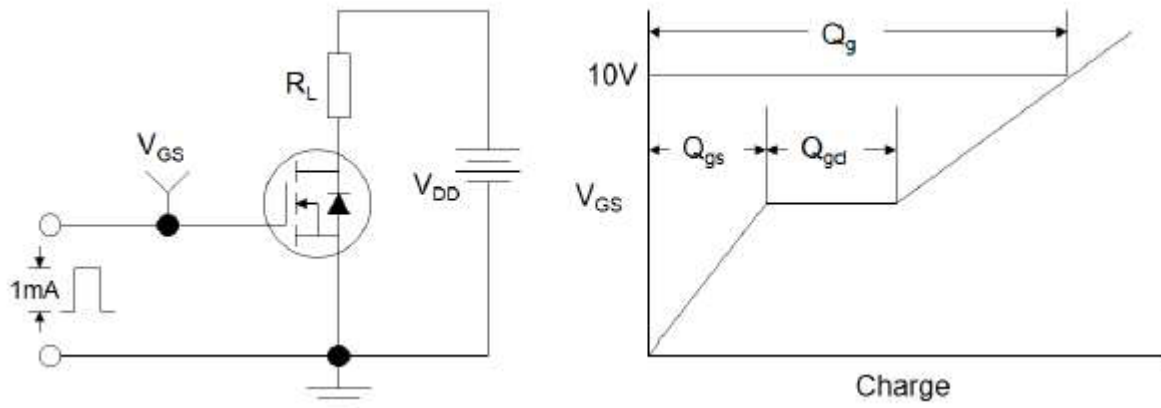


Figure1:Gate Charge Test Circuit & Waveform

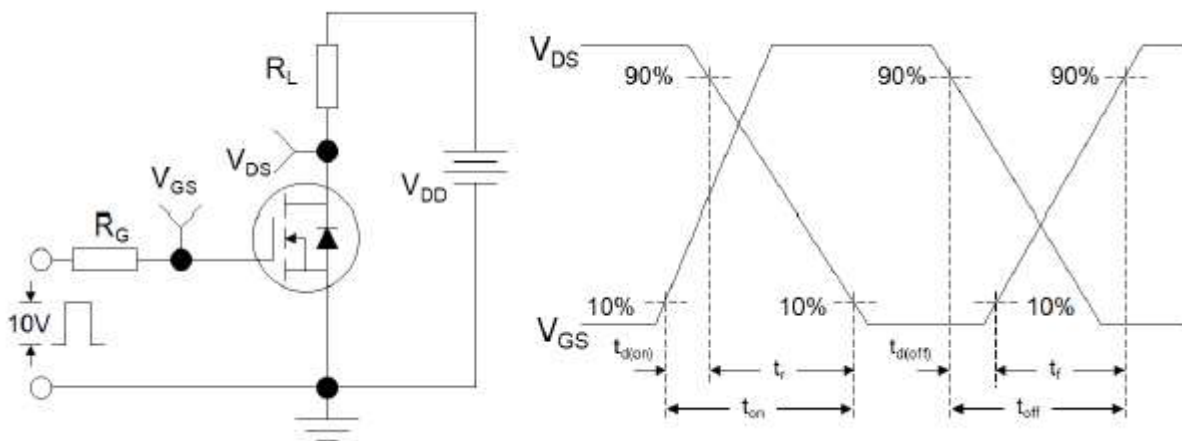


Figure 2: Resistive Switching Test Circuit & Waveforms

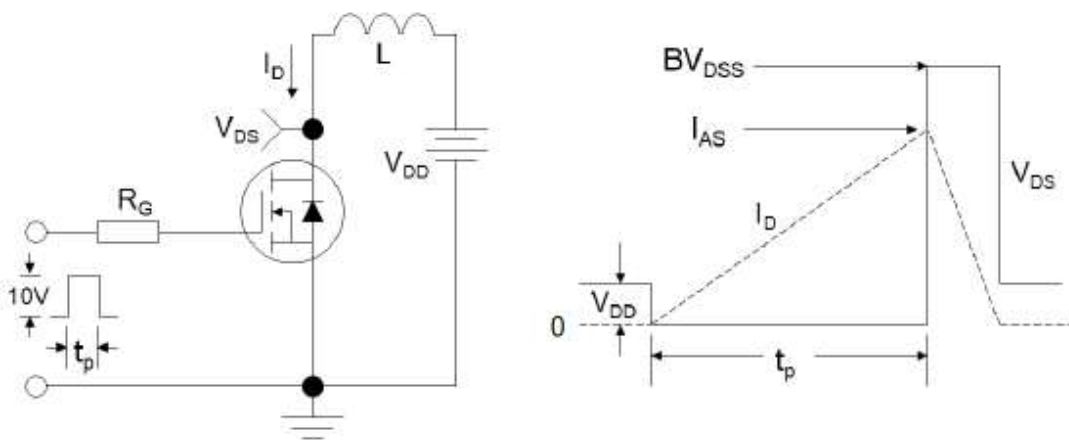


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms